

Publikationen

- (2011): Degradation of polycrystalline HfO₂ based gate dielectrics under nanoscale electrical stress. In: Applied Physics Letters, vol. 99.
- (2011): Nanoscale and Device Level Gate Conduction Variability of High-k Dielectrics-Based Metal-Oxide-Semiconductor Structures. In: IEEE Transactions on Device and Materials Reliability, vol. 11, no. September, pp. 495-501. DOI: 10.1109/TDMR.2011.2161087.
- (2011): Reliability and gate conduction variability of HfO₂-based MOS devices: A combined nanoscale and device level study. In: Microelectronic Engineering, vol. 88, pp. 1334-1337.
- (2011): Conductivity and Charge Trapping After Electrical Stress in Amorphous and Polycrystalline Al₂O₃-Based Devices Studied With AFM-Related Techniques. In: IEEE Transactions on Nanotechnology, vol. 10, no. 2, pp. 344-351.
- (2009): Crystallization and silicon diffusion nanoscale effects on the electrical properties of Al₂O₃ based devices. In: Microelectronic Engineering, vol. 86, no. 7-9, pp. 1921-1924.
- (2009): Crystallization and Silicon Diffusion Nanoscale Effects on the Electrical Properties of Al₂O₃ Based Devices. In: Conference of Insulating Films on semiconductors (INFOS 2009), Cambridge, Großbritannien.